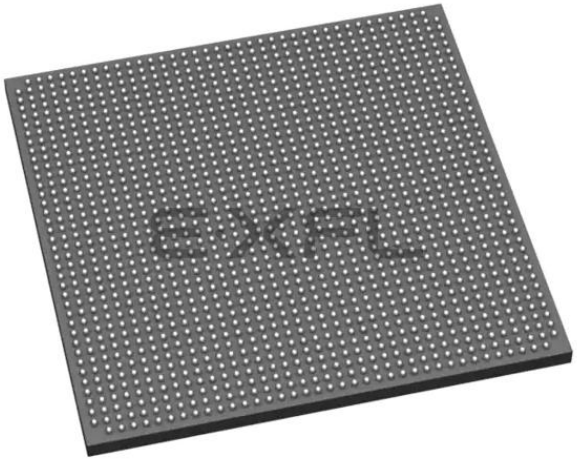
AMD Xilinx - XCZU11EG-3FFVF1517E Datasheet



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What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	600MHz, 667MHz, 1.5GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 653K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	1517-BBGA, FCBGA
Supplier Device Package	1517-FCBGA (40x40)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu11eg-3ffvf1517e

Available Speed Grades and Operating Voltages

Table 3 describes the speed grades per device and the V_{CCINT} operating supply voltages for the full-power, low-power, and DDR domains. For more information on selecting devices and speed grades, see the *UltraScale Architecture and Product Overview* (DS890).

Table 3: **Available Speed Grades and Operating Voltages**

Speed Grade	V_{CCINT}	$V_{CC\_PSINTLP}$	$V_{CC\_PSINTFP}$	$V_{CC\_PSINTFP\_DDR}$	Units
-3E	0.90	0.90	0.90	0.90	V
-2E	0.85	0.85	0.85	0.85	V
-2I	0.85	0.85	0.85	0.85	V
-2LE	0.85	0.85	0.85	0.85	V
-1E	0.85	0.85	0.85	0.85	V
-1I	0.85	0.85	0.85	0.85	V
-1LI	0.85	0.85	0.85	0.85	V
-2LE	0.72	0.85	0.85	0.85	V
-1LI	0.72	0.85	0.85	0.85	V

DC Characteristics Over Recommended Operating Conditions

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).(2)	–	–	15	µA
C_{IN}(3)	Die input capacitance at the pad (HP I/O).	–	–	3.1	pF
	Die input capacitance at the pad (HD I/O).	–	–	4.75	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCONPL}$	Analog supply current for the PL SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCONPS}$	Analog supply current for the PS SYSMON circuits in the power-up state.	–	–	10	mA
$I_{CCADCOFFPL}$	Analog supply current for the PL SYSMON circuits in the power-down state.	–	–	1.5	mA
$I_{CCADCOFFPS}$	Analog supply current for the PS SYSMON circuits in the power-down state.	–	–	1.8	mA

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 5: **PS MIO Pull-up and Pull-down Current**

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 3.3V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 2.5V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 1.8V.	15	65	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 2.5V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	15	65	µA

PS-PL Power Sequencing

The PS and PL power supplies are fully independent. All PS power supplies can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 10 shows the minimum current, in addition to I_{CCQ} maximum, required by each Zynq UltraScale+ device for proper power-on and configuration. If the current minimums shown in Table 10 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 10: **Power-on Current by Device(1)**

I_{CC} Min =	I_{CCQ} +	XCZU2	XCZU3	XCZU4	XCZU5	XCZU6	XCZU7	XCZU9	XCZU11	XCZU15	XCZU17	XCZU19	Units
$I_{CCINTMIN}$	I_{CCINTQ}+	464	464	770	770	1800	1514	1800	1961	2242	3433	3433	mA
I_{CCINT_IOMIN}+ $I_{CCBRAMMIN}$	$I_{CCBRAMQ}$+ I_{CCINT_IOQ}+	155	155	257	257	600	505	600	654	748	1145	1145	mA
I_{CCOMIN}	I_{CCOQ}+	50	50	50	50	50	50	50	55	63	96	96	mA
$I_{CCAUXMIN}$+ I_{CCAUX_IOMIN}	I_{CCAUXQ}+ I_{CCAUX_IOQ}+	111	111	386	386	650	362	650	709	810	1240	1240	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 11 shows the power supply ramp time.

Table 11: **Power Supply Ramp Time**

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT}.	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO}.	0.2	40	ms
T_{VCCINT_VCU}	Ramp time from GND to 95% of V_{CCINT_VCU}.	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO}.	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX}.	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM}.	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms
$T_{VCC\_PSINTFP}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP}$.	0.2	40	ms
$T_{VCC\_PSINTLP}$	Ramp time from GND to 95% of $V_{CC\_PSINTLP}$.	0.2	40	ms
T_{VCC_PSAUX}	Ramp time from GND to 95% of V_{CC_PSAUX}.	0.2	40	ms
$T_{VCC\_PSINTFP\_DDR}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP\_DDR}$.	0.2	40	ms
T_{VCC_PSADC}	Ramp time from GND to 95% of V_{CC_PSADC}.	0.2	40	ms
T_{VCC_PSPLL}	Ramp time from GND to 95% of V_{CC_PSPLL}.	0.2	40	ms
$T_{PS\_MGTRAVCC}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVCC}$.	0.2	40	ms
$T_{PS\_MGTRAVTT}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVTT}$.	0.2	40	ms

PL I/O Levels

Table 14: **SelectIO DC Input and Output Levels For HD I/O Banks(1)(2)(3)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.0	–8.0
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.0	–8.0
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.700	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVCMOS33	–0.300	0.800	2.000	3.400	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVTTL	–0.300	0.800	2.000	3.400	0.400	2.400	Note 5	Note 5
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	14.25	–14.25
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.9	–8.9
SSTL135_II	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.0	–13.0
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.9	–8.9
SSTL15_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.0	–13.0
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.0	–8.0
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.4	–13.4
MIPI_DPHY_DCI_LP(6)	–0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	–0.01

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 16, Table 20, Table 21, and Table 22.
4. Supported drive strengths of 4, 8, or 12 mA in HD I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HD I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 26 correlates the current status of the Zynq UltraScale+ MPSoC on a per speed grade basis. See Table 3 for operating voltages listed by speed grade.

Table 26: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCZU2CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU2EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU3EG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU4CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU4EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	**Preliminary**	**Production**
XCZU11EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU15EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU17EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU19EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		

Notes:

1. The lowest power -1L and -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -1LV and -2LV respectively.

Table 30: **PS DDR Performance *(Cont'd)***

Memory Standard	Package	DRAM Type	Speed Grade						Units
			-3		-2		-1		
			Min	Max	Min	Max	Min	Max	
DDR3	All FFV packages, FBVB900 and SFVC784	Single rank component	664	2133	664	2133	664	2133	Mb/s
		1 rank DIMM(1)(2)	664	1866	664	1866	664	1866	Mb/s
		2 rank DIMM(1)(3)	664	1600	664	1600	664	1600	Mb/s
	SFVA625	Single rank component	664	1866	664	1866	664	1866	Mb/s
		1 rank DIMM(1)(2)	664	1600	664	1600	664	1600	Mb/s
		2 rank DIMM(1)(3)	664	1333	664	1333	664	1333	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM(1)(2)	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
DDR3L	All FFV packages, FBVB900 and SFVC784	Single rank component	664	1866	664	1866	664	1866	Mb/s
		1 rank DIMM(1)(2)	664	1600	664	1600	664	1600	Mb/s
		2 rank DIMM(1)(3)	664	1333	664	1333	664	1333	Mb/s
	SFVA625	Single rank component	664	1600	664	1600	664	1600	Mb/s
		1 rank DIMM(1)(2)	664	1333	664	1333	664	1333	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM(1)(2)	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
LPDDR3	All FFV packages, FBVB900 and SFVC784	Single die package(6)	664	1600	664	1600	664	1600	Mb/s
		Dual die package(6)	664	1333	664	1333	664	1333	Mb/s
	SFVA625	Single die package(6)	664	1333	664	1333	664	1333	Mb/s
		Dual die package(6)	664	1066	664	1066	664	1066	Mb/s
	SBVA484	Single die package(6)	664	1066	664	1066	664	1066	Mb/s
		Dual die package(6)	664	1066	664	1066	664	1066	Mb/s

Notes:

1. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, and UDIMM.
2. Includes: 1 rank 1 slot, dual-die package 2 rank.
3. Includes: 2 rank 1 slot.
4. Dual die package includes single die with ECC.
5. LPDDR4 support is only available as a 32-bit interface.
6. 64-bit LPDDR3 interface performance values are defined without ECC support.

PS Switching Characteristics

PS Clocks

Table 34: **PS Reference Clock Requirements**(1)

Symbol	Description	Min	Typ	Max	Units
$T_{RMSJPSCLK}$	PS_REF_CLK input RMS clock jitter.	–	–	3	ps
$T_{PJPSCLK}$	PS_REF_CLK input period jitter (peak-to-peak). Number of clock cycles = 10,000	–	–	50	ps
$T_{DCPSCLK}$	PS_REF_CLK duty cycle.	45	–	55	%
$T_{RFPSCLK}$	PS_REF_CLK rise time (20%–80%) and fall time (80%–20%).	–	–	2.22	ns
F_{PSCLK}	PS_REF_CLK frequency.	27	–	60	MHz

Notes:

1. The values in this table are applicable to alternative PS reference clock inputs ALT_REF_CLK, AUX_REF_CLK, and VIDEO_CLK.

Table 35: **PS RTC Crystal Requirements**(1)

Symbol	Description	Min	Typ	Max	Units
F_{XTAL}	Parallel resonance crystal frequency.	–	32.8	–	KHz
T_{FTXTAL}	Frequency tolerance.	–20	–	20	ppm
C_{XTAL}	Load capacitance for crystal parallel resonance.	–	12.5	–	pF
R_{ESR}	Crystal ESR (16.8 and 19.2 MHz).	–	70	–	KΩ
C_{SHUNT}	Crystal shunt capacitance.	–	1.4	–	pF

Notes:

1. Required board components: Feedback resistor = 4.7 MΩ, PCB and pad capacitance = 1.5 pF, C_1 and C_2 capacitance = 21 pF.

Table 36: **PS PLL Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{LOCKPSPLL}$	PLL maximum lock time.	100	100	100	µs
$F_{PSPLLMAX}$	PLL maximum output frequency.	1600	1600	1600	MHz
$F_{PSPLLMIN}$	PLL minimum output frequency.	750	750	750	MHz
$F_{PSPLLVCOMAX}$	PLL maximum VCO frequency.	3000	3000	3000	MHz
$F_{PSPLLVCOMIN}$	PLL minimum VCO frequency.	1500	1500	1500	MHz

Table 37: **PS Reset Assertion Timing Requirements**

Symbol	Description	Min	Typ	Max	Units
T_{PSPOR}	Required PS_POR_B assertion time.(1)	10	–	–	µs
T_{PSRST}	Required PS_SRST_B assertion time.	3	–	–	PS_REF_CLK Clock Cycles

Notes:

1. PS_POR_B must be asserted Low at power-up and continue to be asserted for a duration of T_{PSPOR} after all the PS supply voltages reach minimum levels. PS_POR_B must be asserted Low for the duration of T_{POR} when the PS and PL power-up at the same time and the application uses both the PS and PL after power-up.

Table 38: **PS Clocks Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{TOPSW\_MAINMAX}$	TOPSW_MAIN maximum frequency.	600	533	533	MHz
$F_{TOPSW\_LSBUSMAX}$	TOPSW_LSBUS maximum frequency.	100	100	100	MHz
$F_{GDMAMAX}$	FPD-DMA maximum frequency.	600	600	600	MHz
$F_{DPDMAMAX}$	DisplayPort DMA maximum frequency.	600	600	600	MHz
$F_{LPD\_SWITCH\_CTRLMAX}$	LPD_SWITCH_CTRL maximum frequency.	600	500	500	MHz
$F_{LPD\_LSBUS\_CTRLMAX}$	LPD_LSBUS_CTRL maximum frequency.	100	100	100	MHz
$F_{ADMAMAX}$	LPD-DMA maximum frequency.	600	500	500	MHz
$F_{APLL\_TO\_LPDMAX}$	APLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{DPLL\_TO\_LPDMAX}$	DPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{VPLL\_TO\_LPDMAX}$	VPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{IOPLL\_TO\_LPDMAX}$	IOPLL_TO_LPD maximum frequency.	533	533	533	MHz
$F_{RPLL\_TO\_FPDMAX}$	RPLL_TO_FPD maximum frequency.	533	533	533	MHz

PS Configuration

Table 39: **Processor Configuration Access Port Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{PCAPCK}	Maximum processor configuration access port (PCAP) frequency.	200	200	200	150	150	MHz

Table 40: **Boundary-Scan Port Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
F_{TCK}	JTAG clock maximum frequency.	25	25	25	15	15	MHz
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI setup and hold.	4.0/2.0	4.0/2.0	4.0/2.0	5.0/2.0	5.0/2.0	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output.	16.1	16.1	16.1	24	24	ns, Max

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength.

PS I2C Controller Interface

Table 47: **I2C Interface(1)**

Symbol	Description	Min	Max	Units
I2C Fast-mode Interface				
$T_{I2CFCKL}$	SCL Low time.	1.3	–	µs
$T_{I2CFCKH}$	SCL High time.	0.6	–	µs
$T_{I2CFCKO}$	SDA clock to out delay.	–	900	ns
$T_{I2CFDCK}$	SDA input setup time.	100	–	ns
$F_{I2CFCLK}$	SCL clock frequency.	–	400	KHz
I2C Standard-mode Interface				
$T_{I2CSCKL}$	SCL Low time.	4.7	–	µs
$T_{I2CSCKH}$	SCL High time.	4.0	–	µs
$T_{I2CSCKO}$	SDA clock to out delay.	–	3450	ns
$T_{I2CSDCK}$	SDA input setup time.	250	–	ns
$F_{I2CSCLK}$	SCL clock frequency.	–	100	KHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

PS SPI Controller Interface

Table 48: **SPI Interfaces**(1)

Symbol	Description	Min	Max	Units
SPI Master Interface				
$T_{DCMSPICLK}$	SPI master mode clock duty cycle.	45	55	%
$T_{MSPISSSCLK}$	Slave select asserted to first active clock edge.	1(2)	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{MSPISCLKSS}$	Last active clock edge to slave select deasserted.	1(2)	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{MSPIDCK}$	Input setup time for MISO.	–2.0	–	ns
$T_{MSPICKD}$	Input hold time for MISO.	0.3	–	$F_{MSPICLK}$ cycles
$T_{MSPICKO}$	MOSI and slave select clock to out delay.	–2.0	5.0	ns
$F_{MSPICLK}$	SPI master device clock frequency.	–	50	MHz
$F_{SPI\_REF\_CLK}$	SPI reference clock frequency.	–	200	MHz
SPI Slave Interface				
$T_{SSPISSSCLK}$	Slave select asserted to first active clock edge.	2	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{SSPISCLKSS}$	Last active clock edge to slave select deasserted.	2	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{SSPIDCK}$	Input setup time for MOSI.	5.0	–	ns
$T_{SSPICKD}$	Input hold time for MOSI.	1	–	$F_{SPI\_REF\_CLK}$ cycles
$T_{SSPICKO}$	MISO clock to out delay.	0.0	13.0	ns
$F_{SSPICLK}$	SPI slave mode device clock frequency.	–	25	MHz
$F_{SPI\_REF\_CLK}$	SPI reference clock frequency.	–	200	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 30 pF load.
2. Valid when two SPI_REF_CLK delays are programmed between CS and CLK for $T_{MSPISSSCLK}$, and between CLK and CS for $T_{MSPISCLKSS}$ in the SPI delay_reg0 register.

PS CAN Controller Interface

Table 49: **CAN Interface**(1)

Symbol	Description	Min	Max	Units
$T_{PWCANRX}$	Receive pulse width.	1.0	–	µs
$T_{PWCANTX}$	Transmit pulse width.	1.0	–	µs
$F_{CAN\_REF\_CLK}$	Internally sourced CAN reference clock frequency.	–	100	MHz
	Externally sourced CAN reference clock frequency.	–	40	MHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

Table 74: **Maximum Physical Interface (PHY) Rate for Memory Interfaces *(Cont'd)***

Memory Standard	Package(1)	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
DDR3L	All FFV packages and FBVB900	Single rank component	1866	1866	1866	1866	1600	Mb/s
		1 rank DIMM(2)(3)	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM(2)(5)	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM(2)(6)	800	800	800	800	606	Mb/s
	SFVC784	Single rank component	1600	1600	1600	1600	1600	Mb/s
		1 rank DIMM(2)(3)	1600	1600	1600	1600	1333	Mb/s
		2 rank DIMM(2)(5)	1333	1333	1333	1333	1066	Mb/s
		4 rank DIMM(2)(6)	800	800	800	800	606	Mb/s
QDR II+	All	Single rank component(7)	633	633	600	600	550	MHz
RLDRAM 3	All FFV packages and FBVB900	Single rank component	1200	1200	1066	1066	933	MHz
	SFVC784	Single rank component	1066	1066	933	933	800	MHz
QDR IV XP	All	Single rank component	1066	1066	1066	933	933	MHz
LPDDR3	All	Single rank component	1600	1600	1600	1600	1600	Mb/s

Notes:

1. The SBVA484 and SFVA625 packages do not support the PL memory interfaces.
2. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, UDIMM, and LRDIMM.
3. Includes: 1 rank 1 slot, DDP 2 rank, LRDIMM 2 or 4 rank 1 slot.
4. For the DDR4 DDP components at -3 and -2 speed grades and V_{CCINT} = 0.85V, the maximum data rate is 2133 Mb/s for six or more DDP devices. For five or less DDP devices, use the single rank DIMM data rates for the -3 and -2 speed grades at 0.85V.
5. Includes: 2 rank 1 slot, 1 rank 2 slot, LRDIMM 2 rank 2 slot.
6. Includes: 2 rank 2 slot, 4 rank 1 slot.
7. The QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations.

Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

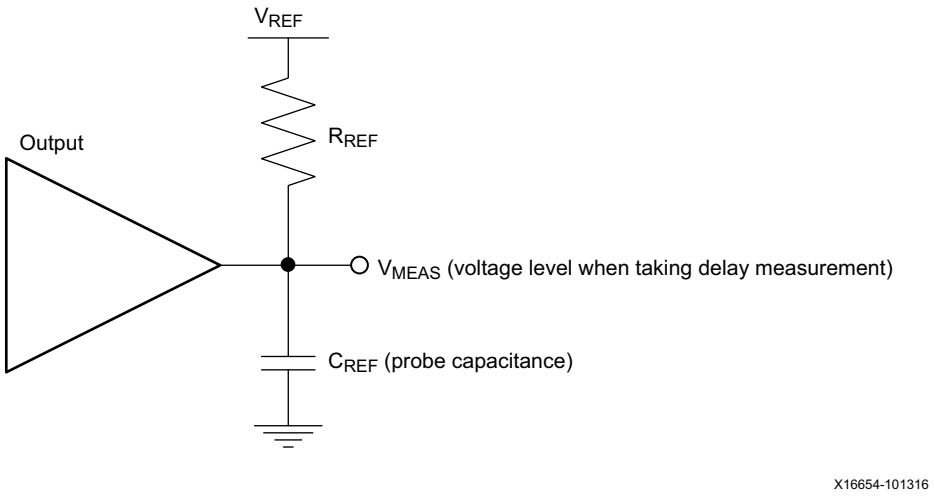

Figure 1: **Single-Ended Test Setup**

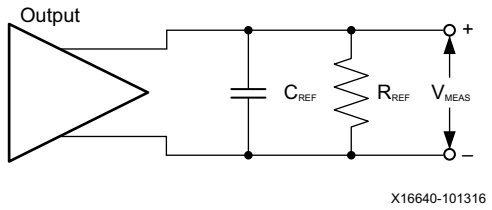

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 79.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Table 79: **Output Delay Measurement Methodology**

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}[1] (pF)	V_{MEAS} (V)	V_{REF} (V)
LVCMOS, 1.2V	LVCMOS12	1M	0	0.6	0
LVCMOS, 1.5V	LVCMOS15	1M	0	0.75	0
LVCMOS, 1.8V	LVCMOS18	1M	0	0.9	0
LVCMOS, 2.5V	LVCMOS25	1M	0	1.25	0
LVCMOS, 3.3V	LVCMOS33	1M	0	1.65	0
LVTTL, 3.3V	LVTTL	1M	0	1.65	0
LVDCI, HSLVDCI, 1.5V	LVDCI_15, HSLVDCI_15	50	0	V_{REF}	0.75
LVDCI, HSLVDCI, 1.8V	LVDCI_15, HSLVDCI_18	50	0	V_{REF}	0.9
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	50	0	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	50	0	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	50	0	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	50	0	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	50	0	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	50	0	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	50	0	V_{REF}	0.75
SSTL18, class I and class II, 1.8V	SSTL18_I, SSTL18_II	50	0	V_{REF}	0.9
POD10, 1.0V	POD10	50	0	V_{REF}	1.0
POD12, 1.2V	POD12	50	0	V_{REF}	1.2
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	50	0	V_{REF}	0.6
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	50	0	V_{REF}	0.75
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	50	0	V_{REF}	0.9
DIFF_HSUL, 1.2V	DIFF_HSUL_12	50	0	V_{REF}	0.6
DIFF_SSTL12, 1.2V	DIFF_SSTL12	50	0	V_{REF}	0.6
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	50	0	V_{REF}	0.675
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	50	0	V_{REF}	0.75
DIFF_SSTL18, class I and II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	50	0	V_{REF}	0.9
DIFF_POD10, 1.0V	DIFF_POD10	50	0	V_{REF}	1.0
DIFF_POD12, 1.2V	DIFF_POD12	50	0	V_{REF}	1.2
LVDS (low-voltage differential signaling), 1.8V	LVDS	100	0	0[2]	0
SUB_LVDS, 1.8V	SUB_LVDS	100	0	0[2]	0
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	100	0	0[2]	0
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	1M	0	0.6	0

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

Table 103: **GTH Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$T_{J2.5}$	Total jitter(3)(4)	2.5 Gb/s(6)	–	–	0.20	UI
$D_{J2.5}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J1.25}$	Total jitter(3)(4)	1.25 Gb/s(7)	–	–	0.15	UI
$D_{J1.25}$	Deterministic jitter(3)(4)		–	–	0.06	UI
T_{J500}	Total jitter(3)(4)	500 Mb/s(8)	–	–	0.10	UI
D_{J500}	Deterministic jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTH Quad) at the maximum line rate.
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of 10^{-12}.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
8. CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 104: **GTH Transceiver Receiver Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHRX}	Serial data rate		0.500	–	F_{GTHMAX}	Gb/s
R_{XSST}	Receiver spread-spectrum tracking(1)	Modulated at 33 kHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)		–	–	256	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$J_{T\_SJ16.375}$	Sinusoidal jitter (QPLL)(3)	16.375 Gb/s	0.30	–	–	UI
$J_{T\_SJ15.0}$	Sinusoidal jitter (QPLL)(3)	15.0 Gb/s	0.30	–	–	UI
$J_{T\_SJ14.1}$	Sinusoidal jitter (QPLL)(3)	14.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ13.1}$	Sinusoidal jitter (QPLL)(3)	13.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ12.5}$	Sinusoidal jitter (QPLL)(3)	12.5 Gb/s	0.30	–	–	UI
$J_{T\_SJ11.3}$	Sinusoidal jitter (QPLL)(3)	11.3 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_QPLL}$	Sinusoidal jitter (QPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_CPLL}$	Sinusoidal jitter (CPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_QPLL}$	Sinusoidal jitter (QPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_CPLL}$	Sinusoidal jitter (CPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ8.0}$	Sinusoidal jitter (QPLL)(3)	8.0 Gb/s	0.42	–	–	UI
$J_{T\_SJ6.6\_CPLL}$	Sinusoidal jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$J_{T\_SJ5.0}$	Sinusoidal jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$J_{T\_SJ4.25}$	Sinusoidal jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$J_{T\_SJ3.2}$	Sinusoidal jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI

GTY Transceiver Switching Characteristics

Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further information.

Table 109: **GTY Transceiver Performance**

Symbol	Description	Output Divider	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3		-2		-1		-2		-1		
F_{GTYMAX}	GTY maximum line rate		32.75		28.21		25.7813		28.21		12.5		Gb/s
F_{GTYMIN}	GTY minimum line rate		0.5		0.5		0.5		0.5		0.5		Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYCRANGE}$	CPLL line rate range(1)	1	4.0	12.5	4.0	12.5	4.0	8.5	4.0	12.5	4.0	8.5	Gb/s
		2	2.0	6.25	2.0	6.25	2.0	4.25	2.0	6.25	2.0	4.25	Gb/s
		4	1.0	3.125	1.0	3.125	1.0	2.125	1.0	3.125	1.0	2.125	Gb/s
		8	0.5	1.5625	0.5	1.5625	0.5	1.0625	0.5	1.5625	0.5	1.0625	Gb/s
		16	N/A										Gb/s
		32	N/A										Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYQRANGE1}$	QPLL0 line rate range(2)	1	19.6	32.75	19.6	28.21	19.6	25.7813	19.6	28.21	N/A		Gb/s
		1	9.8	16.375	9.8	16.375	9.8	12.5	9.8	16.375	9.8	12.5	Gb/s
		2	4.9	8.1875	4.9	8.1875	4.9	8.1875	4.9	8.1875	4.9	8.1875	Gb/s
		4	2.45	4.0938	2.45	4.0938	2.45	4.0938	2.45	4.0938	2.45	4.0938	Gb/s
		8	1.225	2.0469	1.225	2.0469	1.225	2.0469	1.225	2.0469	1.225	2.0469	Gb/s
		16	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYQRANGE2}$	QPLL1 line rate range(3)	1	16.0	26.0	16.0	26.0	19.6	25.7813	16.0	26.0	N/A		Gb/s
		1	8.0	13.0	8.0	13.0	8.0	12.5	8.0	13.0	8.0	12.5	Gb/s
		2	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	Gb/s
		4	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	Gb/s
		8	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	Gb/s
		16	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{CPLLRANGE}$	CPLL frequency range		2.0	6.25	2.0	6.25	2.0	4.25	2.0	6.25	2.0	4.25	GHz
$F_{QPLL0RANGE}$	QPLL0 frequency range		9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	GHz
$F_{QPLL1RANGE}$	QPLL1 frequency range		8.0	13.0	8.0	13.0	8.0	13.0	8.0	13.0	8.0	13.0	GHz

Notes:

1. The values listed are the rounded results of the calculated equation (2 x CPLL_Frequency)/Output_Divider.
2. The values listed are the rounded results of the calculated equation (2 x QPLL0_Frequency)/Output_Divider.
3. The values listed are the rounded results of the calculated equation (2 x QPLL1_Frequency)/Output_Divider.

Table 115: **GTY Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$T_{J3.20}$	Total jitter(3)(4)	3.20 Gb/s(5)	–	–	0.20	UI
$D_{J3.20}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J2.5}$	Total jitter(3)(4)	2.5 Gb/s(6)	–	–	0.20	UI
$D_{J2.5}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J1.25}$	Total jitter(3)(4)	1.25 Gb/s(7)	–	–	0.15	UI
$D_{J1.25}$	Deterministic jitter(3)(4)		–	–	0.06	UI
T_{J500}	Total jitter(3)(4)	500 Mb/s(8)	–	–	0.10	UI
D_{J500}	Deterministic jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTY Quad) at maximum line rate.
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of 10^{-12}.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
8. CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Revision History

The following table shows the revision history for this document.

Date	Version	Description of Revisions
04/20/2017	1.3	Updated Table 25, Table 26, and Table 27 to production release for the following devices/speed/temperature grades in Vivado Design Suite 2017.1. XCZU2CG and XCZU2EG: –2E, -2I, -1E, -1I XCZU3CG and XCZU3EG: –2E, -2I, -1E, -1I XCZU6CG and XCZU6EG: –2E, -2I, -1E, -1I XCZU9CG and XCZU9EG: –2E, -2I, -1E, -1I Added -2E (V_{CCINT} = 0.85V) speed grade where applicable. Removed -3E speed grade from the XCZU2 and XCZU3 devices in Table 26 and where applicable. In Table 1, updated values and Note 2. In Table 2, added or updated many of the notes. Updated Table 4 including the notes and added Note 6. Moved and updated Table 5. Added Table 8. Updated Table 9 and added Note 4. Updated Table 10 and added Note 1. Revised V_{ICM} in Table 23. Updated Table 30 and removed Note 1. Added Table 31 and Table 32. Updated Table 33 and removed F_{FTMCLK}. Updated $T_{RFPSCLK}$ in Table 34. Updated Note 1 in Table 37. Updated Table 39. Removed the *PS NAND Memory Controller Interface* section. Significant changes to Table 41 and removed Note 3. Significant changes to Table 42 and updated Note 1. Removed $F_{TSU\_REF\_CLK}$ from Table 44. Revised Table 45 and added Note 2 and Note 3. Revised Table 46 and added Note 2 and Note 3. Updated Table 48. Updated Table 51 and removed Note 2. Revised Table 52. Revised many of the tables in the PS-GTR Transceiver section. Revised Table 70 and Table 71. Removed Note 8 from Table 74. Updated the values in Table 75, Table 76, Table 77, Table 80, Table 87, Table 88, Table 89, Table 90,and Table 91 to the Vivado Design Suite 2017.1 speed specifications. Updated the values in Table 81 and Table 82. Added values to Table 92. Updated Table 93. Revised D_{VPPOUT} in Table 94. Update the values in Table 96. Added Note 6 to Table 102. Updated Table 103 and Table 104. Revised D_{VPPOUT} in Table 106. Updated the values in Table 108. In Table 109 updated the -1 (0.85V) specifications and removed Note 1. In Table 114 updated the -1 (0.85V) specifications and added Note 6. In Table 115 and Table 116, added the 28.21 jitter tolerance values and revised the notes. Revised the Integrated Interface Block for Interlaken and Integrated Interface Block for 100G Ethernet MAC and PCS sections. Revised the Configuration Switching Characteristics section. Removed the *eFUSE Programming Conditions* table and added the specifications to Table 2 and Table 3.

Date	Version	Description of Revisions
02/10/2017	1.2	Updated some of the maximum voltages in the Processor System (PS) section and other specifications in the Programmable Logic (PL) and GTH or GTY Transceiver sections of Table 1. Updated Table 2, Table 4, Table 6, Table 7, and Table 9. Revised the Power Supply Sequencing section including Table 10. Added PS and VCU ramp times to Table 11. Revised V_{ODIFF} in Table 24. Updated Table 25. Added Note 1 to Table 26. Table 30 replaces the previous three PS memory performance tables. Added values to Table 34, Table 37, and Table 38. Deleted the waveforms in the PS Switching Characteristics section (Figures 1-16 and Figures 25-26). Revised values in the *PS NAND Memory Controller Interface* section. Added and updated data in Table 40. Added Note 3 to Table 41. Added Note 3 to Table 42. Added Note 1 to Table 45. Updated Table 48 and removed Note 3. Added data to Table 56. Updated Table 60. Added Table 61. Updated Table 63. Revised Table 69. Added data to Table 70. Added Note 2 to Table 71. Updated Table 74 and added Note 4. Updated V_L and V_H values in Table 78. Added T_{MINPER_CLK}, revised F_{REFCLK}, and Note 1 to Table 82. Added MMCM_F_{DPRCLK_MAX} to Table 85 and PLL_F_{DPRCLK_MAX} to Table 86. Added data to Table 94, Table 96, Table 98, Table 101, and updated the note references in Table 102. Updated Table 103 and added Note 8. Updated Table 104 and added Note 7. Added more protocols, Note 1 and Note 2 to Table 105. Removed the *GTH Transceiver Protocol Jitter Characteristics* section because it is covered in Table 105. Added Note 1 to Table 109. Added data to Table 106, Table 108, Table 110, Table 113. Added Note 2 to Table 112. Added note references in Table 114. Updated Table 115 and added Note 8. Updated Table 116 and added Note 7. Added more protocols and Note 3 to Table 117. Removed the *GTY Transceiver Protocol Jitter Characteristics* section because it is covered in Table 117. Revised Table 124. Added T_{POR} and updated F_{ICAPCK} in Table 127. Updated the Automotive Applications Disclaimer.
06/20/2016	1.1	Updated the Summary description. In Table 1, revised V_{IN} for HP I/O banks and added clarifications to some descriptions and symbols. Added I_{RPU}, I_{RPD}, and Note 4 to Table 2 and updated $V_{PS\_MGTRAVCC}$, the PL System Monitor section, and Note 3 and Note 5. Updated Note 5 in Table 4. Updated the PS Power-On/Off Power Supply Sequencing section including all the voltage supply names. Added MIPI_DPHY_DCI to Table 14, Table 15, and Table 17. Updated Table 23, including removing the V_{CCO} specification and adding Note 1. Added Note 1 to Table 24. Updated Table 25 speed specifications for Vivado Design Suite 2016.1. Added values to Table 28. Updated the -2 value in Table 29. Added $F_{DPLIVEVIDEO}$ and updated $F_{FCIDMACLK}$ in Table 33. Added VCO frequencies to Table 36. Added the T_{PSPOR} minimum to Table 37 and updated Note 1. Added Table 38. Added value delineation over V_{CCINT} operating voltages in Table 39. Revised values for F_{TCK} and T_{TAPTCK}/T_{TCKTAP} in Table 40 and added value delineation over V_{CCINT} operating voltages. Updated the *PS NAND Memory Controller Interface* section. Revised some units and Note 1 in Table 41 and Table 42. Removed Figure 6: Quad-SPI Interface (Feedback Clock Disabled) Timing. Updated Note 1 of Table 43. Added $F_{TSI\_REF\_CLK}$ to Table 44 and updated Note 1. In Table 45, revised $T_{DCSDHSCLK1}$, $T_{DCSDHSCLK2}$, and $T_{DCSDHSCLK3}$ and Note 1. In Table 46, revised Note 1. In Table 47, revised Note 1. Revised Table 48, including Note 1, and added Note 2 and Note 3. In Table 49, Table 50, Table 51, and Table 53, revised Note 1. Updated Table 71. Replaced Table 74. Updated Table 75 and Table 76. Updated Table 78 and Table 79. In Table 80, added the Block RAM and FIFO Clock-to-Out Delays section. Updated the R_{IN} and C_{EXT} values in Table 57 and Table 95. Updated the -2 (0.72V) and -1 (0.72V) values and added Note 1 to Table 97. Added Table 100 and Table 112. Added Note 2 to Table 106. Revised data in Table 109. Revised Table 114. Revised data and added notes in the Integrated Interface Block for Interlaken section and Table 121. Moved Table 123. Revised INL in Table 124. Added notes to Table 125 and Table 126. In the *eFUSE and Programming Conditions* table, updated the I_{PSFS} description.
11/24/2015	1.0	Initial Xilinx release.